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ITO SPUTTERING TARGET
ABSTRACT

The present invention provides an ITO sputtering target comprising a target produced through a machine grinding step and made of an oxide (ITO) containing at least one of indium oxide and tin oxide and an ITO film having a film thickness of more than 1 μm that is formed on a sputter surface of the target. According to the present invention, a sputtering target capable of effectively reducing occurrence of initial arc and having high initial stability can be obtained. By conducting sputtering using this sputtering target, formation of thin films having high performance can be efficiently carried out with enhanced productivity. Further, since finish grinding is omissible, the grinding step can be simplified and the cost can be decreased.